

What is claimed is:

1. A polishing agent containing at least globular-silica powder and alumina powder.
2. The polishing agent according to claim 1, wherein the average grain diameter of the globular-silica powder is smaller than the average grain diameter of the alumina powder.
3. The polishing agent according to claim 1, wherein the average grain diameter of the globular-silica powder is 2-7 μ m.
4. The polishing agent according to claim 2, wherein the average grain diameter of the globular-silica powder is 2-7 μ m.
5. The polishing agent according to claim 1, wherein the amount of the globular-silica contained in the polishing agent is 20-50 percent by weight.
6. The polishing agent according to claim 2, wherein the amount of the globular-silica contained in the polishing agent is 20-50 percent by weight.
7. The polishing agent according to claim 3, wherein

the amount of the globular-silica contained in the polishing agent is 20-50 percent by weight.

8. The polishing agent according to claim 4, wherein the amount of the globular-silica contained in the polishing agent is 20-50 percent by weight.

9. A lapping method wherein a workpiece is lapped using the polishing agent according to claim 1.

10. A lapping method wherein a workpiece is lapped using the polishing agent according to claim 2.

11. A lapping method wherein a workpiece is lapped using the polishing agent according to claim 3.

12. A lapping method wherein a workpiece is lapped using the polishing agent according to claim 4.

13. A lapping method wherein a workpiece is lapped using the polishing agent according to claim 5.

14. A lapping method wherein a workpiece is lapped using the polishing agent according to claim 6.

15. A lapping method wherein a workpiece is lapped using the polishing agent according to claim 7.

16. A lapping method wherein a workpiece is lapped using the polishing agent according to claim 8.

17. A lapping method in which a workpiece is held between an upper turn table and a lower turn table, the workpiece being lapped by rotating the upper and the lower turn tables while being supplied with a polishing agent, wherein the polishing agent is a polishing agent containing at least globular-silica powder and alumina powder.

18. The lapping method according to claim 9, wherein the workpiece to be lapped is a silicon wafer or a quartz wafer.

19. The lapping method according to claim 17, wherein the workpiece to be lapped is a silicon wafer or a quartz wafer.